



# STB46NF30, STP46NF30, STW46NF30

N-channel 300 V, 0.063  $\Omega$  typ, 42 A, STripFET™ II Power MOSFET  
in D<sup>2</sup>PAK, TO-220 and TO-247 packages

Datasheet — production data

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub>	P <sub>w</sub>
STB46NF30	300 V	< 0.075 $\Omega$	42 A	300 W
STP46NF30	300 V	< 0.075 $\Omega$	42 A	300 W
STW46NF30	300 V	< 0.075 $\Omega$	42 A	300 W

- Exceptional dv/dt capability
- 100% avalanche tested
- Low gate charge

## Applications

- Switching applications
  - Automotive

## Description

These Power MOSFETs have been developed using STMicroelectronics' unique STripFET process, which is specifically designed to minimize input capacitance and gate charge. This renders the devices suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

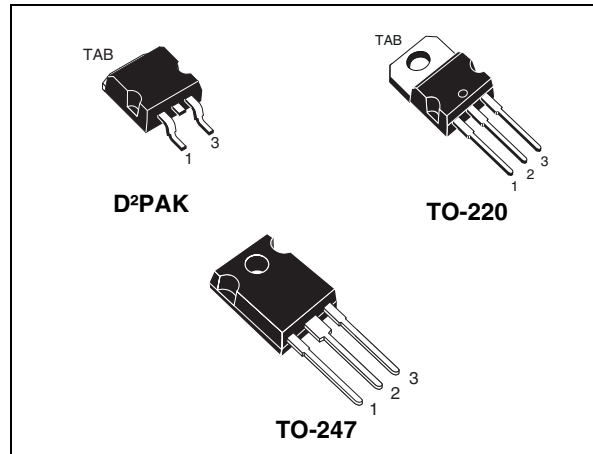


Figure 1. Internal schematic diagram

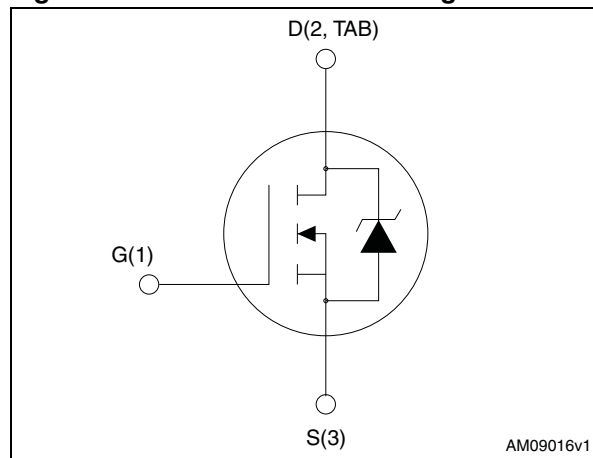


Table 1. Device summary

Order code	Marking	Package	Packaging
STB46NF30	46NF30	D <sup>2</sup> PAK	Tape and reel
STP46NF30	46NF30	TO-220	Tube
STW46NF30	46NF30	To-247	Tube

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	300	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	42	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	27	A
$I_{DM}^{(1)}$	Drain current (pulsed)	168	A
$P_{tot}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
$dv/dt^{(2)}$	Peak diode recovery voltage slope	10	V/ns
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	175	$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2.  $I_{SD} \leq 34\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 80\% V_{(BR)DSS}$ .

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		D <sup>2</sup> PAK	TO-220	TO-247	
$R_{thj-case}$	Thermal resistance junction-case max	0.5			$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	30	62.5	50	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max	30			$^\circ\text{C}/\text{W}$
$T_J$	Maximum lead temperature for soldering purpose	300			$^\circ\text{C}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive <sup>(1)</sup>	26	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	290	mJ

1. Pulse width limited by  $T_{jmax}$
2. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AR}$ ,  $V_{DD} = 50\text{ V}$

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	300			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 300\text{ V}$ $V_{DS} = 300\text{ V}$ , $T_C = 125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 17\text{ A}$		0.063	0.075	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	3200	-	pF
$C_{oss}$	Output capacitance			442		pF
$C_{rss}$	Reverse transfer capacitance			57		pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 150\text{ V}$ , $I_D = 17\text{ A}$ $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 16</a> )	-	25	-	ns
$t_r$	Rise time			38		ns
$t_{d(off)}$	Turn-off delay time			80		ns
$t_f$	Fall time			46		ns
$Q_g$	Total gate charge	$V_{DD} = 240\text{ V}$ , $I_D = 34\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 17</a> )	-	90	-	nC
$Q_{gs}$	Gate-source charge			16		nC
$Q_{gd}$	Gate-drain charge			40		nC

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		34 136	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 34 \text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 34 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 18</a> )	-	215 1.7 16		ns nC A
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 34 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 60 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 18</a> )	-	252 2.3 19		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D<sup>2</sup>PAK and TO-220

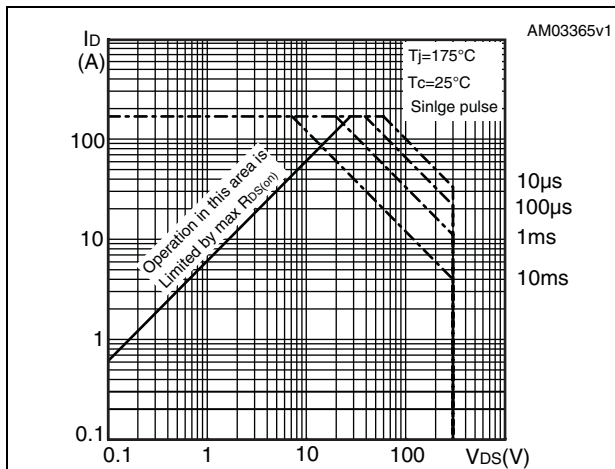


Figure 3. Thermal impedance for D<sup>2</sup>PAK and TO-220

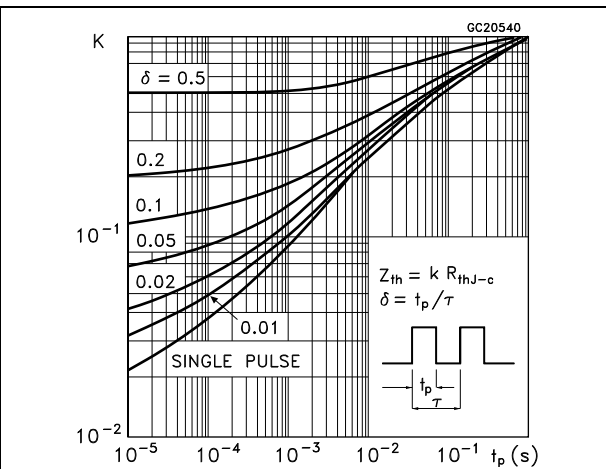


Figure 4. Safe operating area for TO-247

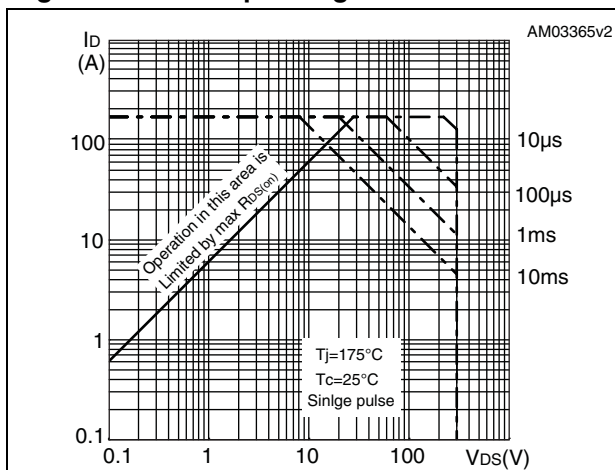


Figure 5. Thermal impedance for TO-247

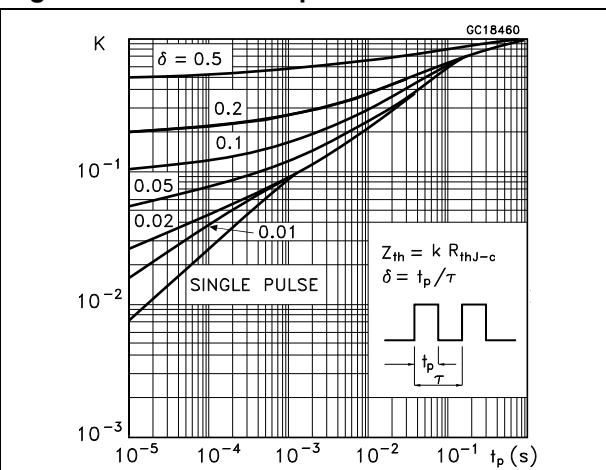


Figure 6. Output characteristics

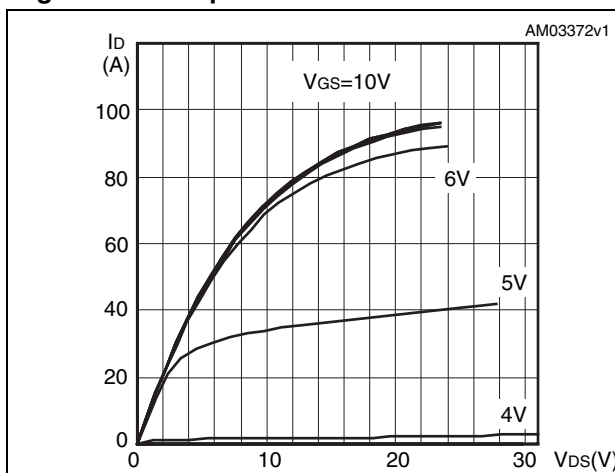


Figure 7. Transfer characteristics

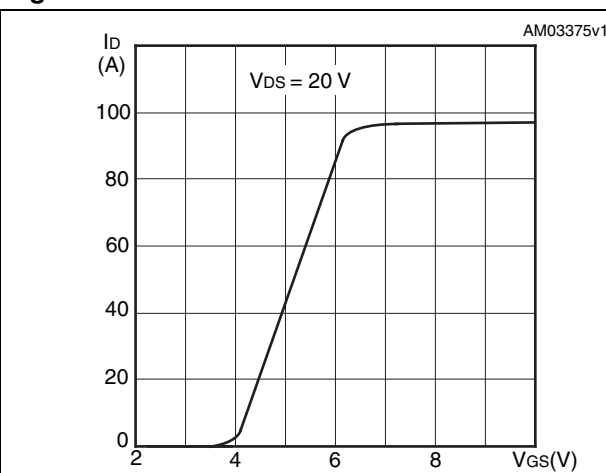


Figure 8. Normalized  $BV_{DSS}$  vs temperature

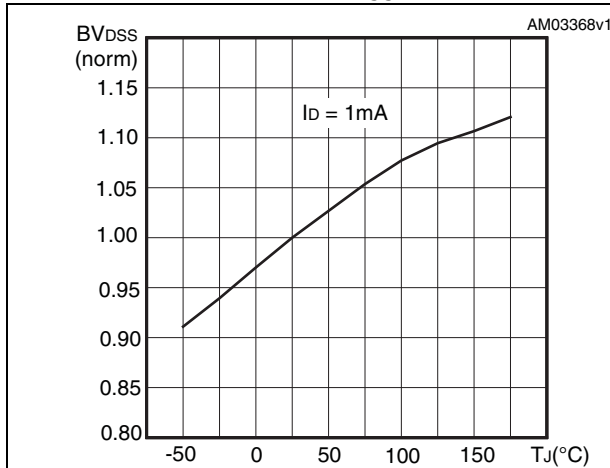


Figure 9. Static drain source on-resistance

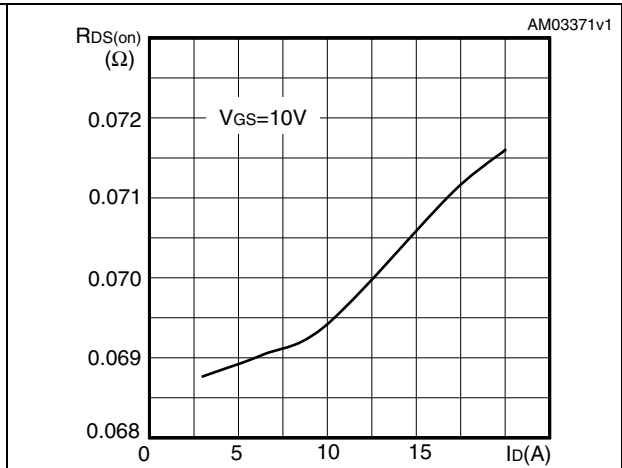


Figure 10. Gate charge vs gate-source voltage

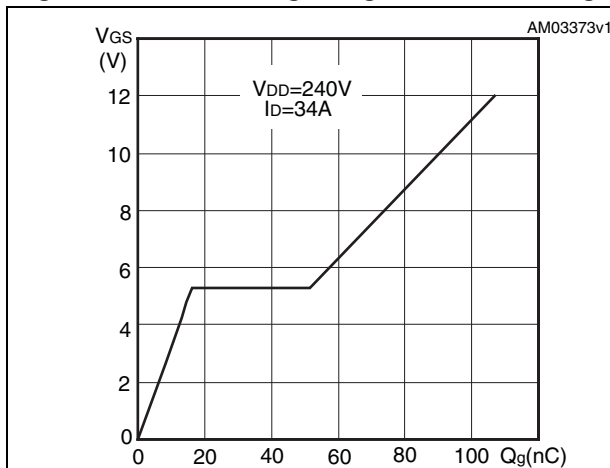


Figure 11. Capacitance variations

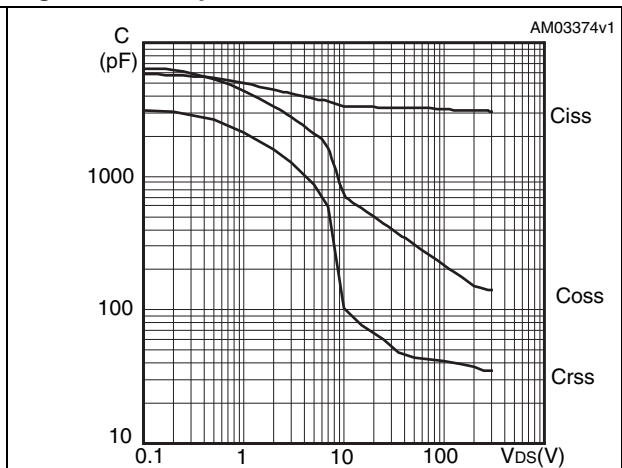


Figure 12. Normalized gate threshold voltage vs temperature

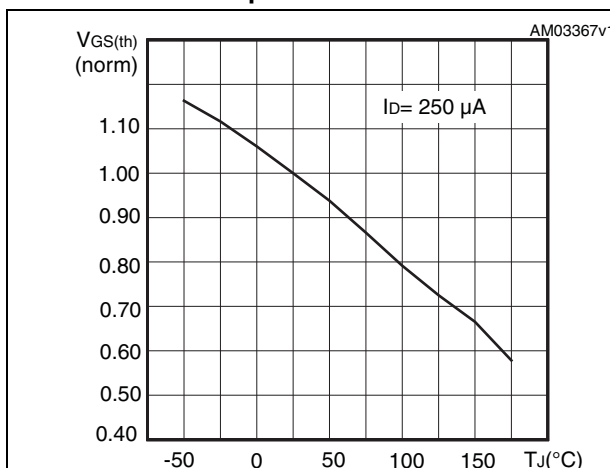


Figure 13. Normalized on resistance vs temperature

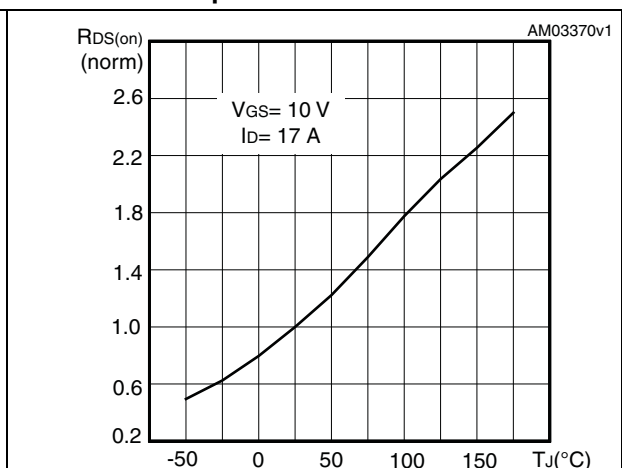


Figure 14. Source-drain diode forward characteristics

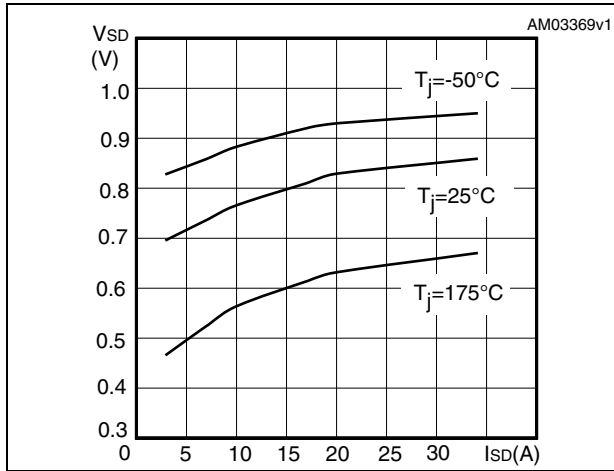
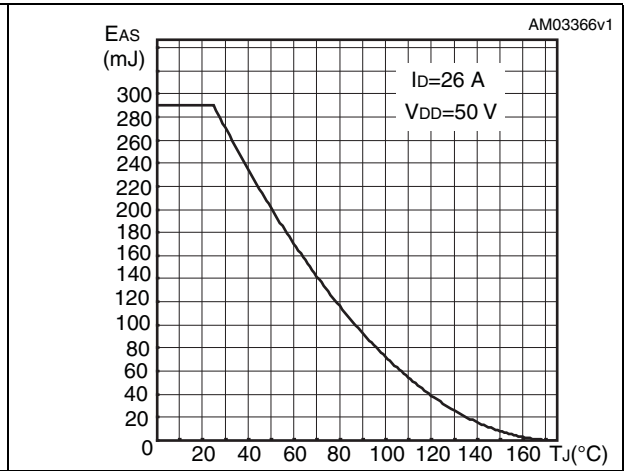


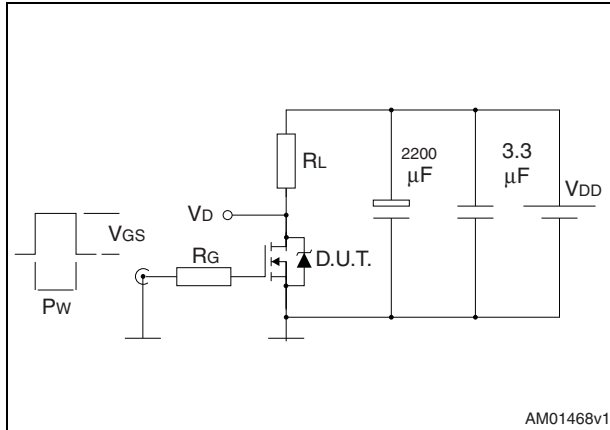
Figure 15. Avalanche energy vs starting T<sub>j</sub>





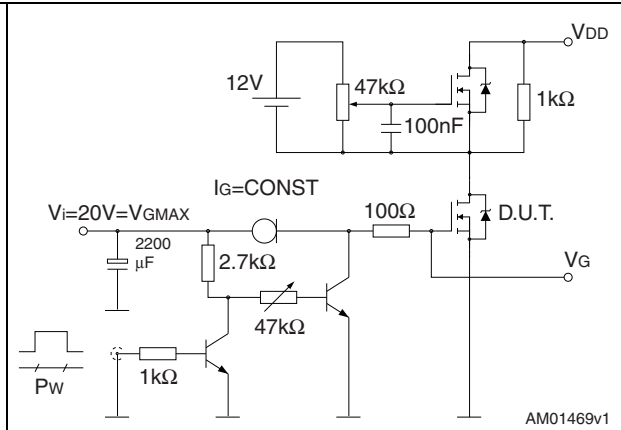
### 3 Test circuits

**Figure 16. Switching times test circuit for resistive load**



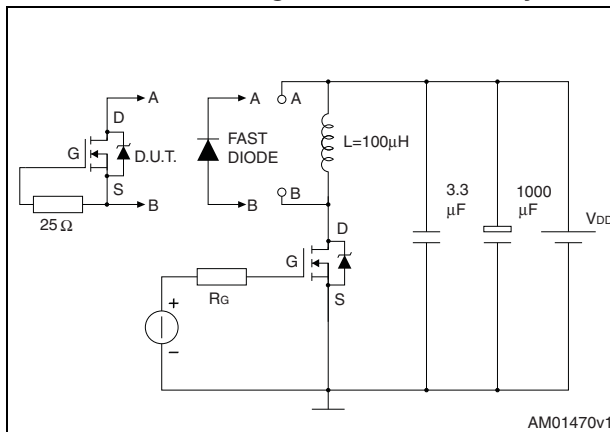
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**Figure 17. Gate charge test circuit**



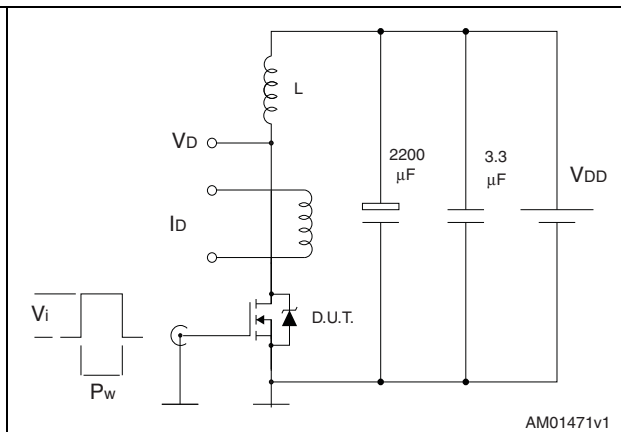
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**Figure 18. Test circuit for inductive load switching and diode recovery times**



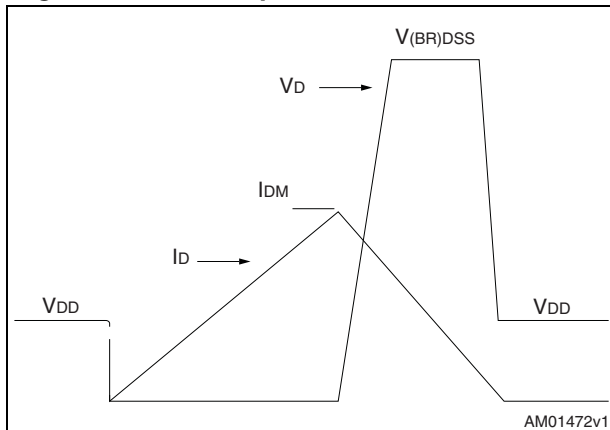
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**Figure 19. Unclamped inductive load test circuit**



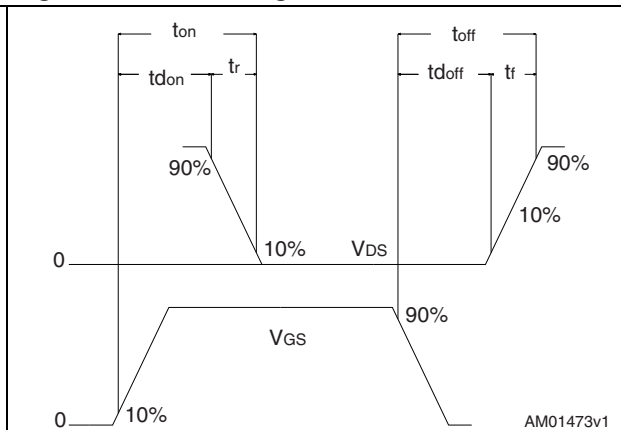
AM01471v1

**Figure 20. Unclamped inductive waveform**



AM01472v1

**Figure 21. Switching time waveform**



AM01473v1

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

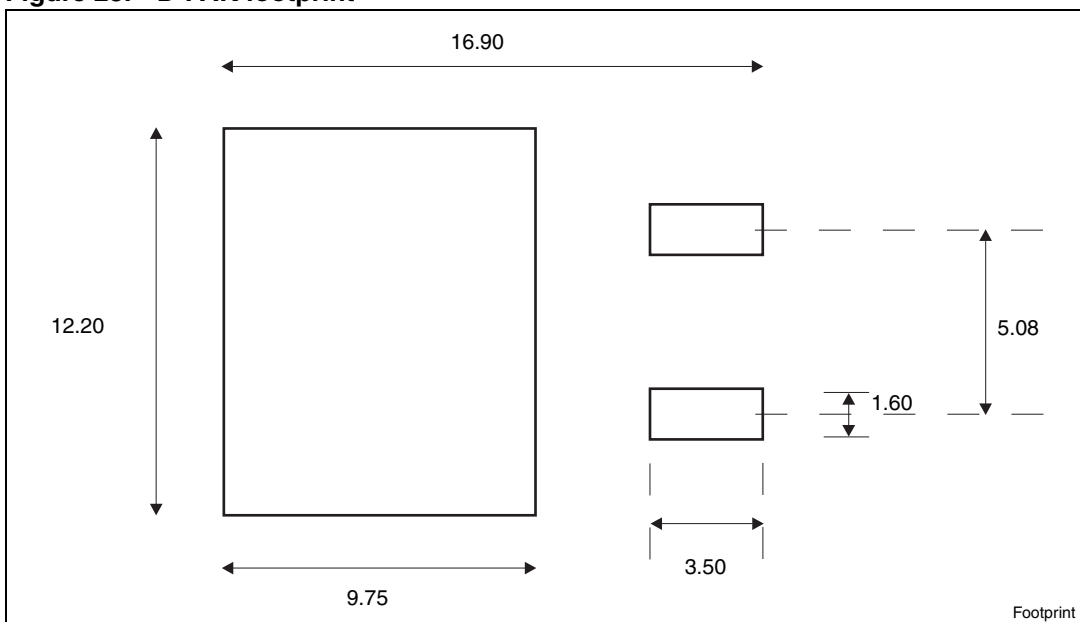
**Table 8. D<sup>2</sup>PAK (TO-263) mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 22. D<sup>2</sup>PAK (TO-263) drawing



Figure 23. D<sup>2</sup>PAK footprint<sup>(a)</sup>



a. All dimension are in millimeters

Table 9. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 24. TO-220 type A drawing

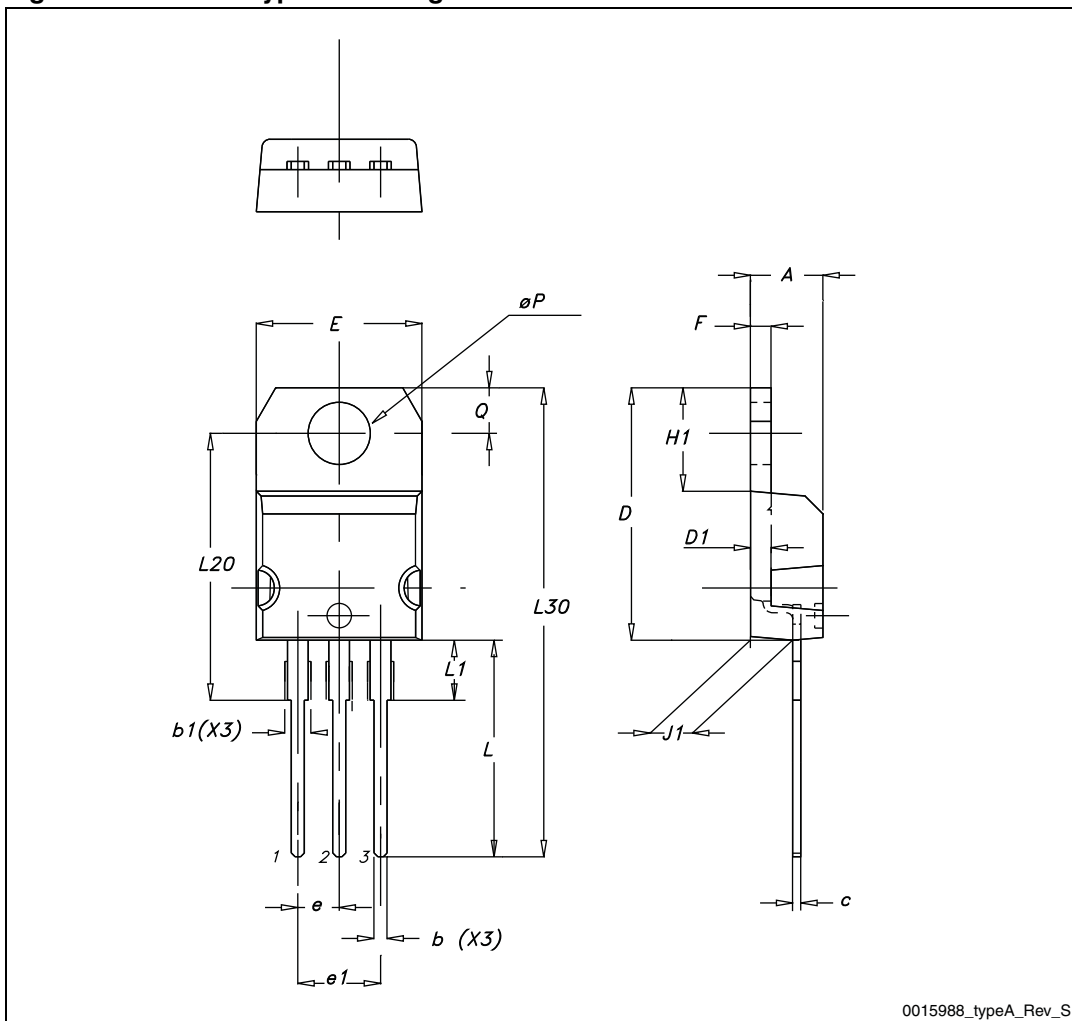
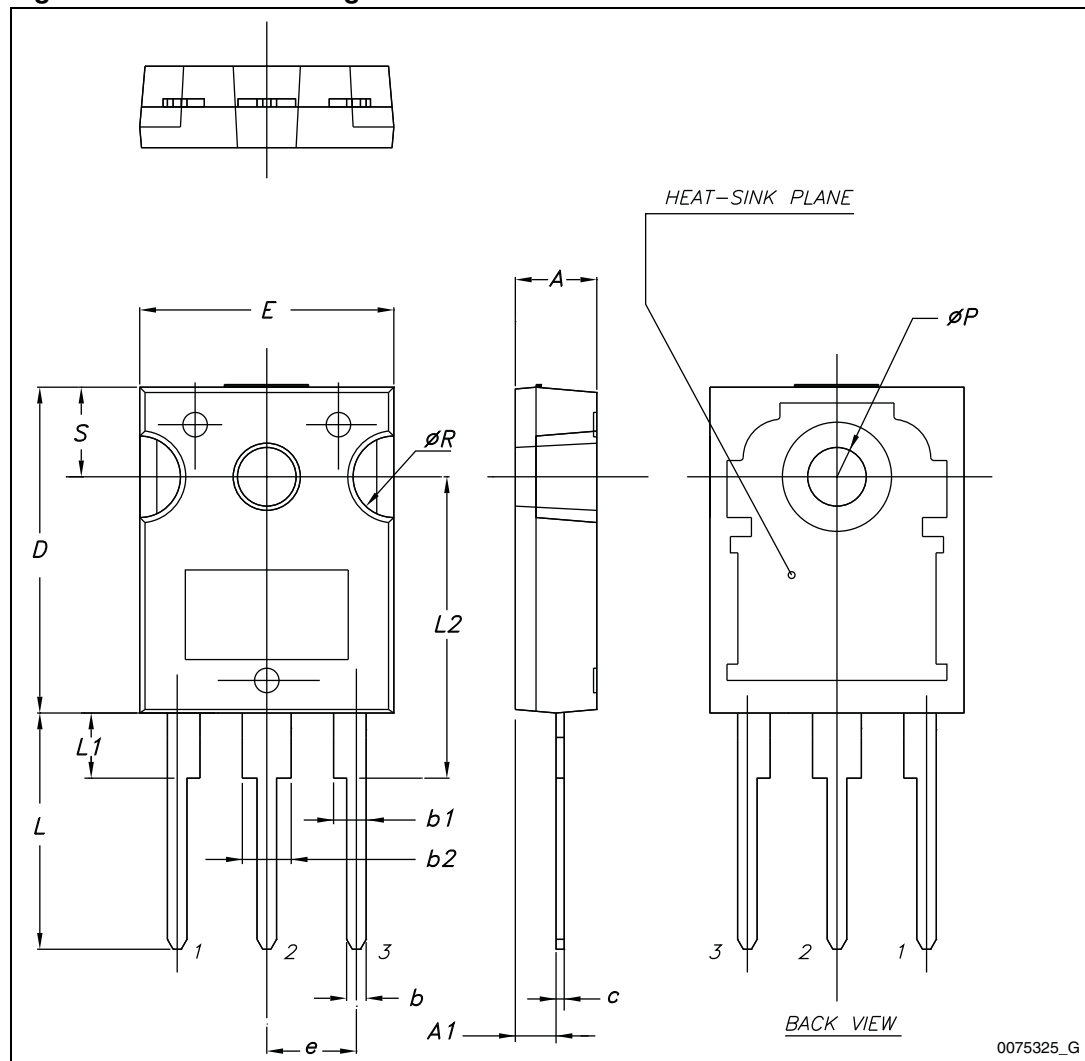


Table 10. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 25. TO-247 drawing



0075325\_G

## 5 Packaging mechanical data

Table 11. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			



Figure 26. Tape

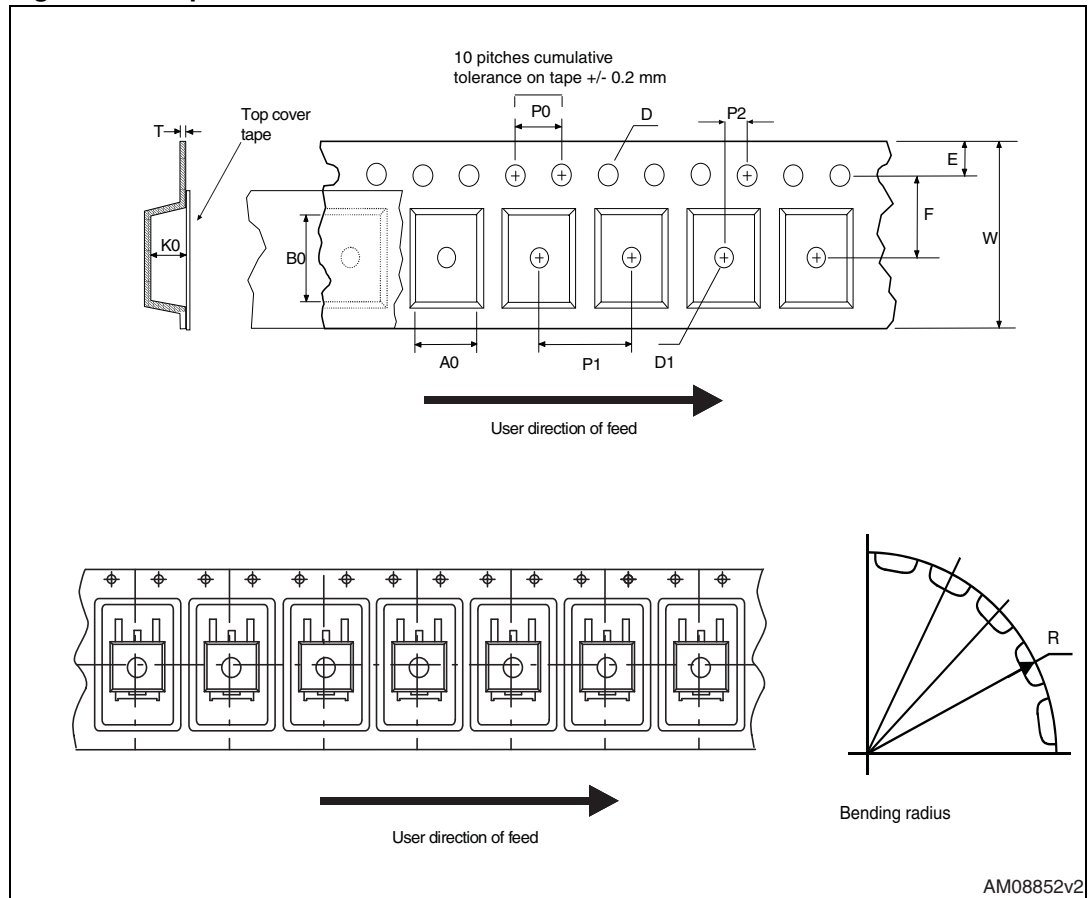
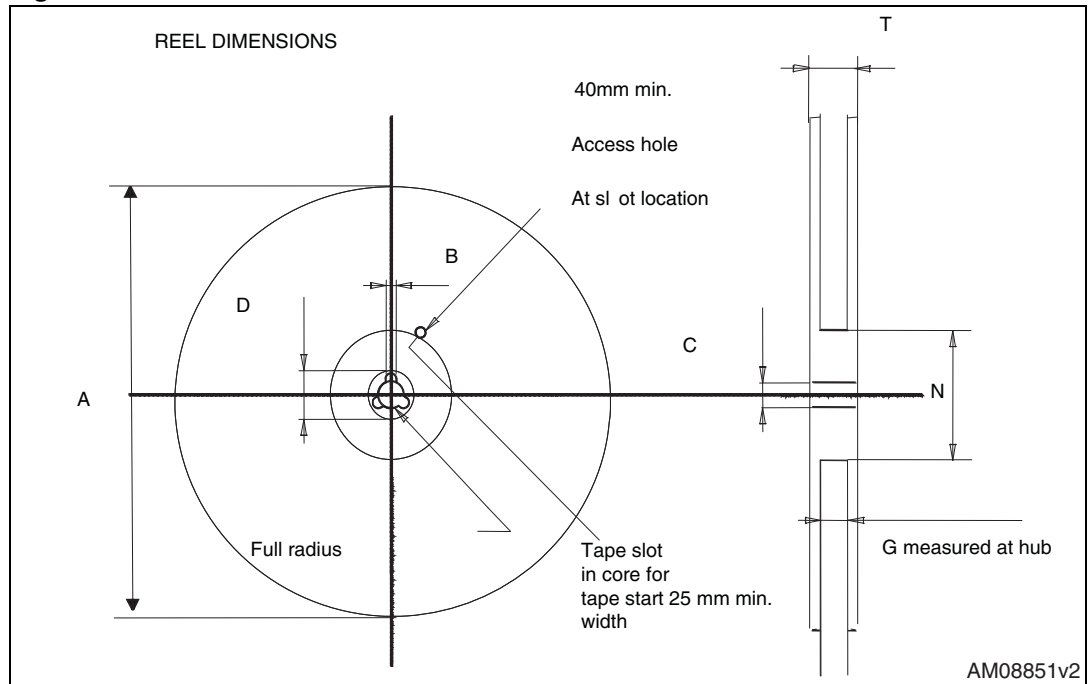


Figure 27. Reel



## 6 Revision history

Table 12. Document revision history

Date	Revision	Changes
28-Sep-2012	1	First release.

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